IN THE CLAIMS

Please amend the claims as set forth below in marked-up form below.

1. (Currently Amended) An exposure method for projecting a desired pattern on an object to be exposed utilizing a reflective mask for an exposure light, comprising the steps of: providing respective reflective [mask] masks each having a mask pattern consisting of only pattern forming elements of the same direction with regard to the respective longitudinal direction by dividing pattern forming elements of the mask pattern corresponding to said desired pattern relative to a projection vector of the exposure light; sequentially carrying out projection of said mask pattern on said object to be exposed by irradiating said exposure light and its reflection light with regard to the respective reflective mask in the respective direction; and rotating, when one reflective mask is changed to [the other] an other reflective mask, said other reflective mask and said object to be exposed so that an angle of the pattern forming elements of said other reflective mask and the projection vector becomes equal to an angle of the pattern forming elements of said one reflective mask and the projection vector.

2. (Currently amended) The exposure method as cited in Claim 1, wherein said reflective mask of the respective direction includes a V-line mask having a pattern only including the pattern forming elements perpendicular to said projection [vector,]vector and an H-line mask having a pattern only including the pattern forming elements horizontal to said projection vector.

3. (Original) The exposure method as cited in Claim 1, wherein said exposure light is one of a charged particle beam, an X-ray, an Extreme Ultra Violet ray, an Ultra Violet ray, and a visible light.

4. (Original) The exposure method as cited in Claim 3, wherein said charged particle beam is one of an electron beam and an ion beam.

5. (Original) The exposure method as cited in Claim 2, wherein a perpendicular direction of the mask pattern including the pattern forming elements formed on said V-line mask relative to said projection vector corresponds to an scanning direction of an exposure apparatus.

6. (Original) The exposure method as cited in Claim 1, wherein a rotation angle of said rotation is approximately 90 degrees with regard to said object to be exposed.

7. (Original) The exposure method as cited in Claim 1, wherein said projection process is sequentially carried out twice or more than twice.

8. (Original) A mask fabrication method for projecting a desired pattern on an object to be exposed utilizing a reflective mask for an exposure light, comprising the steps of: dividing pattern forming elements of a mask pattern corresponding to said desired pattern with regard to respective direction relative to a projection vector of the exposure light; forming respective reflective mask each having a mask pattern

consisting of only pattern forming elements of the same direction with regard to the respective direction; and forming respective reflective mask of respective direction so that when the reflective mask and said object to be exposed are rotated relative to said projection vector, an angle of the pattern forming elements of respective reflective mask and the projection vector is always the same.

9. (Original) The mask fabrication method as cited in Claim 8, wherein said reflective mask of the respective direction includes a V-line mask having a pattern only including the pattern forming elements perpendicular to said projection vector, and an H-line mask having a pattern only including the pattern forming elements horizontal to said projection vector.

10. (Original) The mask fabrication method as cited in Claim 8, wherein said exposure light is one of a charged particle beam, an X-ray, an Extreme Ultra Violet ray, an Ultra Violet ray, and a visible light.

11. (Original) The mask fabrication method as cited in Claim 10, wherein said charged particle beam is one of an electron beam and an ion beam.

12. (Currently amended) The mask fabrication method as cited in Claim 9, wherein a perpendicular direction of the mask pattern including the pattern forming elements formed on said V-line mask relative to said projection vector corresponds to [an] a scanning direction of an exposure apparatus.

13. (Currently amended) The mask fabrication method as cited in Claim 9, wherein said dividing process for the mask pattern corresponding to the desired pattern includes: erasing desired size data in the X direction with the [under] under-size or over-size only in the X direction from [an] input design data; extracting H-line data which is graphic data of only the X direction; and extracting the rest of graphic data by subtracting the graphic data of only the X direction from said input design data as V-line data so that said rest of the graphic data corresponds to the V-line data extending in Y direction.

14. (Original) The mask fabrication method as cited in Claim 8, wherein a rotation angle of said rotation is approximately 90 degrees with regard to said object to be exposed.

15. (Currently amended) A fabrication method of a semiconductor device including a lithography process for projecting a desired pattern on an object to be exposed using a reflective mask for an exposure light, comprising the steps of: providing respective reflective [mask] masks each having a mask pattern consisting of only pattern forming elements of the same direction with regard to the respective direction by dividing pattern forming elements of the mask pattern corresponding to said desired pattern relative to a projection vector of the exposure light; sequentially carrying out projection of said mask pattern on said object to be exposed by irradiating said exposure light and its reflection light with regard to the respective reflective mask in the respective direction; and rotating, when one reflective mask is changed to the other

reflective mask, said other reflective mask and said object to be exposed so that an angle of the pattern forming elements of said [the] other reflective mask and the projection vector becomes equal to an angle of the pattern forming elements of said one reflective mask and the projection vector.

16. (Original) The fabrication method of a semiconductor device as cited in Claim 15, wherein said reflective mask of the respective direction includes a V-line mask having a pattern only including the pattern forming elements perpendicular to said projection vector, and an H-line mask having a pattern only including the pattern forming elements horizontal to said projection vector.

17. (Original) The fabrication method of a semiconductor device as cited in Claim 15, wherein said exposure light is one of a charged particle beam, an X-ray, an Extreme Ultra Violet ray, an Ultra Violet ray, and a visible light.

18. (Original) The fabrication method of a semiconductor device as cited in Claim 17, wherein said charged particle beam is one of an electron beam and an ion beam.

19. (Original) The fabrication method of a semiconductor device as cited in Claim 16, wherein a perpendicular direction of the mask pattern including the pattern forming elements formed on said V-line mask relative to said projection vector corresponds to an operating direction of an exposure apparatus.

20. (Original) The fabrication method of a semiconductor device as cited in Claim 15, wherein a rotation angle of said

rotation is approximately 90 degrees with regard to said object to be exposed.